

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SC1391

DESCRIPTION

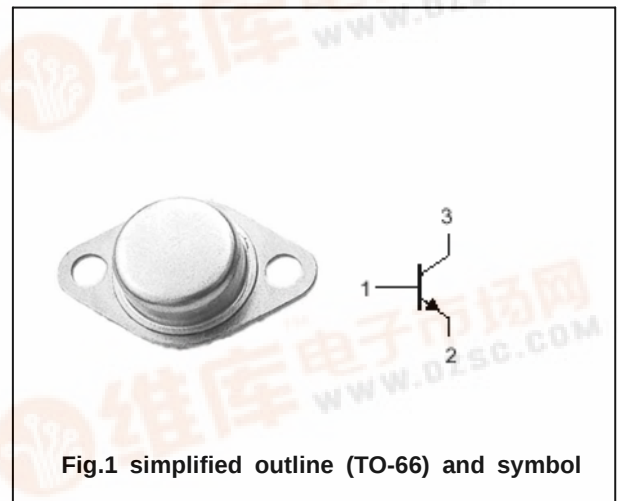
- With TO-66 package
- High collector-emitter voltage
- $V_{CE0}=300V$

APPLICATIONS

- For use in line-operated color TV chroma output circuits and sound output circuits.

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings ($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	300	V
V_{CEO}	Collector-emitter voltage	Open base	300	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		0.1	A
P_T	Collector power dissipation	$T_C=25^{\circ}C$	6.5	W
T_j	Junction temperature		150	$^{\circ}C$
T_{stg}	Storage temperature		-55~150	$^{\circ}C$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=50\text{ }\mu\text{ A}$; $I_E=0$	300			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=1\text{mA}$; $I_B=0$	300			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=50\text{ }\mu\text{ A}$; $I_C=0$	5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=50\text{mA}$; $I_B=5\text{mA}$			2.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=300\text{V}$; $I_E=0$			5	$\mu\text{ A}$
I_{EBO}	Emitter cut-off current	$V_{EB}=7\text{V}$; $I_C=0$			5	$\mu\text{ A}$
h_{FE}	DC current gain	$I_C=50\text{mA}$; $V_{CE}=10\text{V}$	30		160	
f_T	Transition frequency	$I_C=10\text{mA}$; $V_{CE}=20\text{V}$	25			MHz

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PACKAGE OUTLINE

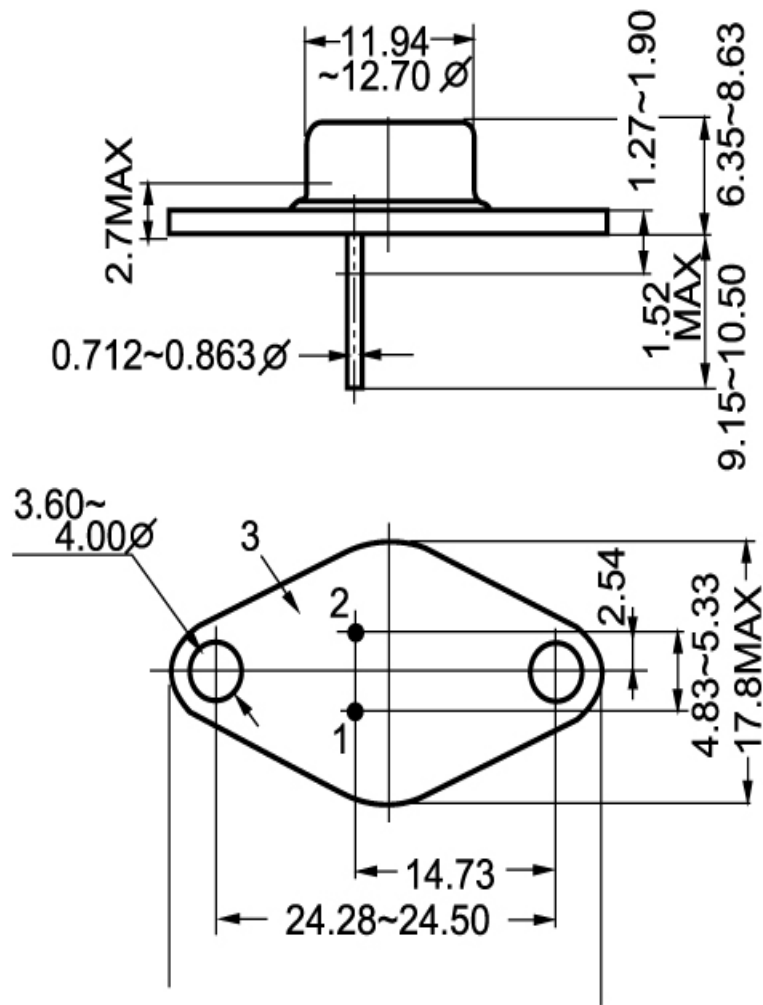


Fig.2 outline dimensions (unindicated tolerance: $\pm 0.10 \text{ mm}$)